UNIKC
Semiconductor

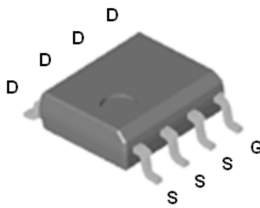
RoHS Compliant

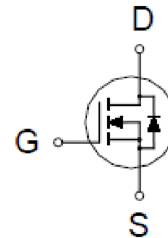
PA110BV

N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	110mΩ @V_{GS} = 10V	3.2A





SOP-8

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25 °C	I_D	3.2	A
	T_A = 70 °C		2.5	
Pulsed Drain Current[1]		I_{DM}	10	
Avalanche Current		I_{AS}	25	
Avalanche Energy	L =0.1mH	E_{AS}	31	mJ
Power Dissipation	T_A = 25 °C	P_D	2.5	W
	T_A = 70 °C		1.6	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		50	°C / W

[1]Pulse width limited by maximum junction temperature.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMIT MIN	TYP	MAX	UNITS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	2	3	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
		V_{DS} = 80V, V_{GS} = 0V, T_J = 55 °C			10	μA
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 2A		99	120	mΩ
		V_{GS} = 10V , I_D = 2A		93	110	mΩ
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 2A		20		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz		1350		pF
Output Capacitance	C_{oss}			90		pF
Reverse Transfer	C_{rss}			55		pF
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1.25		Ω
Total Gate Charge[2]	Q_g (V_{GS} =10V)	V_{DS} = 0.5$V_{(BR)DSS}$, V_{GS} = 10V, I_D = 2A		28		nC
	Q_g (V_{GS} =4.5V)			15		nC
Gate-Source Charge[2]	Q_{gs}			3.5		nC
Gate-Drain Charge[2]	Q_{gd}			7		nC
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 50V,R_L = 25Ω, I_D ≅ 2A, V_{GS} = 10V, R_{GEN} = 6Ω		14		nS
Rise Time[2]	t_r			14		nS
Turn-Off Delay Time[2]	$t_{d(off)}$			15		nS
Fall Time[2]	t_f			12		nS
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				1.8	A
Forward Voltage[1]	V_{SD}	I_F = 2A, V_{GS} = 0V			1.4	V
Reverse Recovery Time	t_{rr}	I_F = 2A, dI_F/dt = 100A / μS		40		nS
Reverse Recovery Charge	Q_{rr}			39		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

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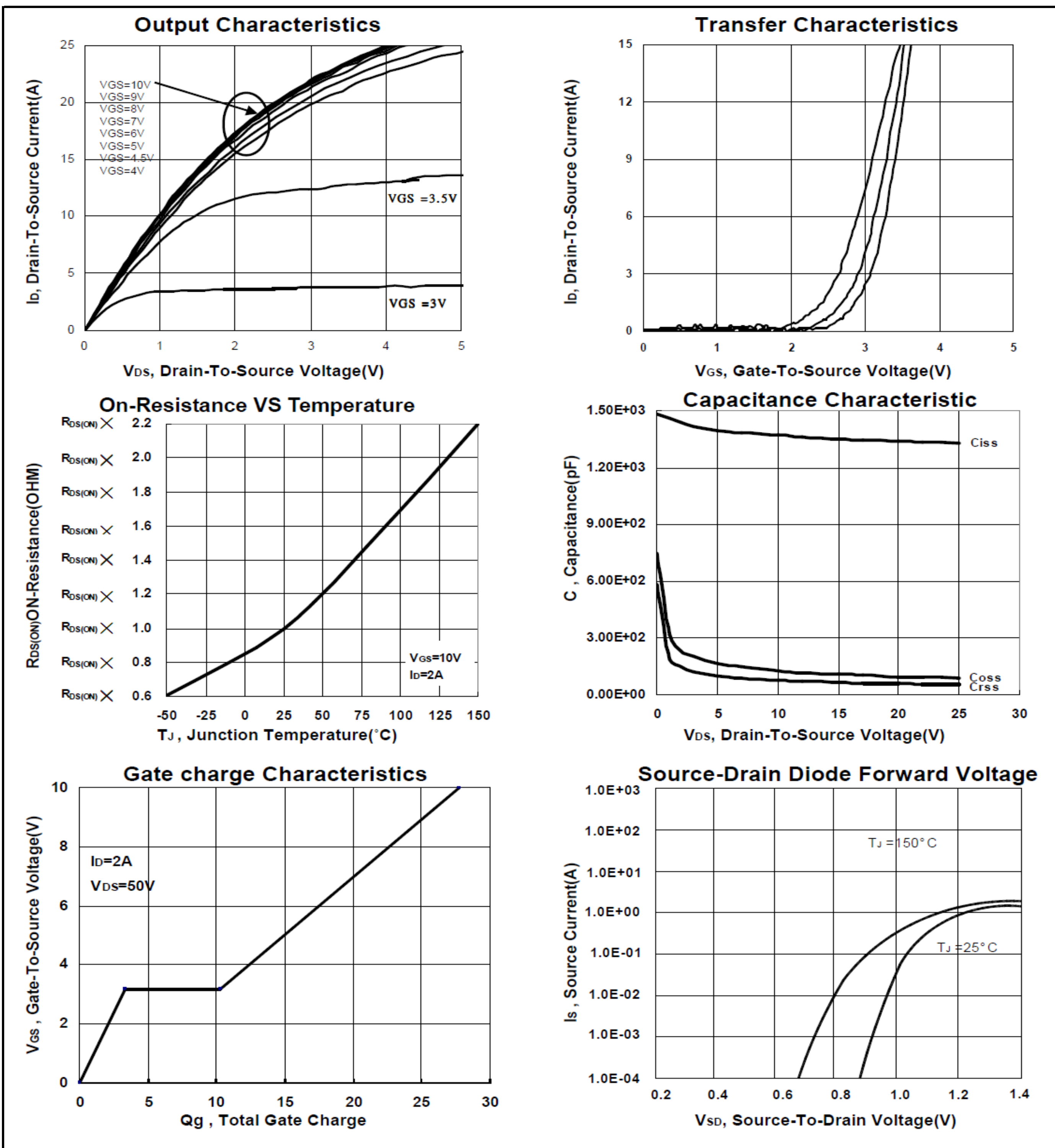

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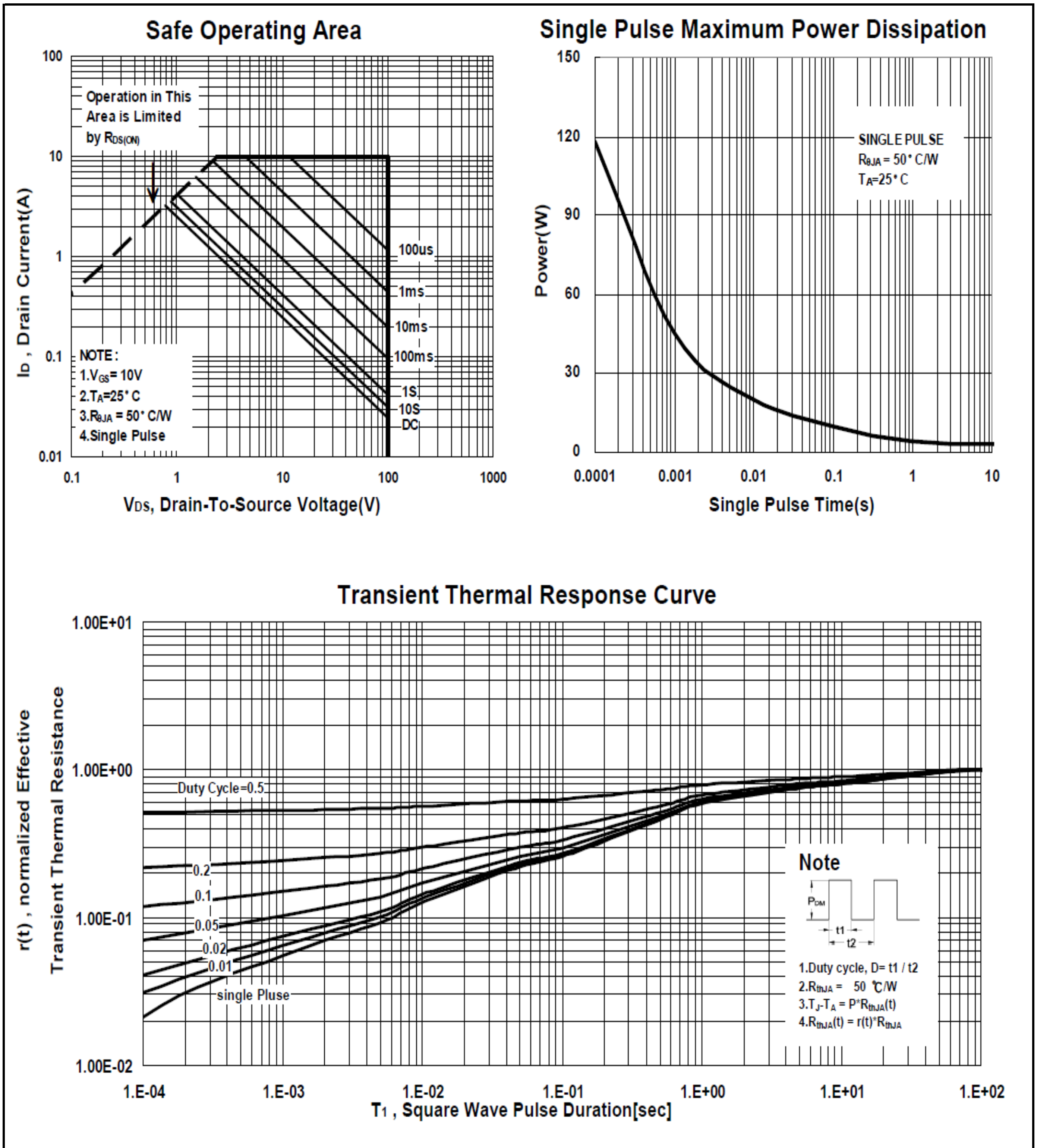

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SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25